Amendment

In the title:

Please amend the title of the invention to read as follows: – Organic EL Device –.

In the Specification:

Please enter the following amendments.

On page 8, lines 12-21, please replace the paragraph with the following:

Thereafter, a first metal layer is deposited on the gate insulating layer 420 using, for example, a sputtering technique to a predetermined thickness. The first metal layer comprises a metal such as aluminum (Al) and aluminum-neodymium alloy (Al:Nd). As shown in Figs. 5, 6 and 19 the first metal layer is patterned to form a first gate electrode 120 of the first TFT 100, a second gate electrode 220 of the second TFT 200, a first capacitor electrode 310 of the storage capacitor 300, and a gate line 430. Subsequently, an n-type or a p-type impurity is ion-implanted into the first and second semiconductor layers 110 and 220 to form a first source region 130 and a first drain region 140 of the first TFT 100 and a second source region 240 and a second drain region 230 of the second TFT 200.

Please replace the paragraph bridging from page 8, line 22 to page 9, line 12 with the following:

In more detail, on a portion of the gate insulating layer 420 corresponding to the

first semiconductor layer 110, the first gate electrode 120 having an area size smaller than the first semiconductor layer 110 is formed. The gate line 430 is arranged in a transverse direction spaced apart from the first semiconductor layer 110 and is connected to the first gate electrode 120. At this point, the first semiconductor layer 110 includes the source region 130 and the drain region 140, respectively, formed on both end portions thereof. The first capacitor electrode 310 is formed between the first gate electrode 120 and the second gate electrode 220 in such a way that it is spaced apart from the drain region 140 of the first semiconductor layer 110 and is connected to the second gate electrode 220. On a portion of the gate insulating layer 420 corresponding to the second semiconductor layer 210, the second gate electrode 220 having a smaller area size than the second semiconductor layer 210 is formed. At this point, the second semiconductor layer 210 includes the drain region 230 and the source region 240, respectively, formed on both end portions thereof.

On page 10, lines 6-11, please replace the paragraph with the following:

Subsequently, a second metal layer is deposited on the interlayer insulator 440 using, for example, a sputtering technique. As shown in Figs. 11, 12 and 19, the second metal layer is patterned to form a first source electrode 182 and a first drain electrode 184 of the first TFT 100, a second source electrode 282 and a second drain electrode 284 of the second TFT 200, a second capacitor electrode 330 of the storage capacitor 300, a data line 450, and a common power line 460.